

SEMICONDUCTOR TECHNICAL DATA

2N5401C

EPITAXIAL PLANAR PNP TRANSISTOR

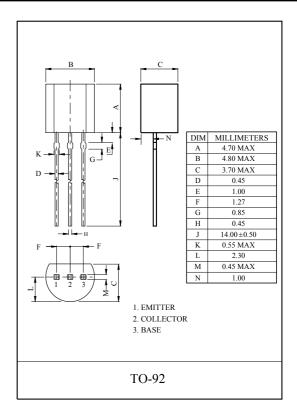
GENERAL PURPOSE APPLICATION. HIGH VOLTAGE APPLICATION.

FEATURES

- · High Collector Breakdwon Voltage
 - : V_{CBO} =-160V, V_{CEO} =-150V
- · Low Leakage Current.
 - : I_{CBO} =-50nA(Max.) @ V_{CB} =-120V
- · Low Saturation Voltage
 - : $V_{CE(sat)}$ =-0.5V(Max.) @ I_{C} =-50mA, I_{B} =-5mA
- · Low Noise: NF=8dB (Max.)

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-160	V
Collector-Emitter Voltage	V _{CEO}	-150	V
Emitter-Base Voltage	$V_{\rm EBO}$	-5	V
Collector Current	I_{C}	-600	mA
Base Current	I_{B}	-100	mA
Collector Power Dissipation (Ta=25℃)	P_{C}	625	mW
Collector Power Dissipation (Tc=25℃)	P _C	1.5	W
Junction Temperature	Tj	150	${\mathbb C}$
Storage Temperature Range	T_{stg}	-55~150	$^{\circ}$



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ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	т	V_{CB} =-120V, I_{E} =0	-	-	-50	nA	
		I_{CBO}	V_{CB} =-120V, I_{E} =0, Ta =100°C	-	-	-50	μ A
Emitter Cut-off Current		I_{EBO}	V_{EB} =-3V, I_C =0	-	-	-50	nA
Collector-Base Breakdown Voltage		V _{(BR)CBO}	I_{C} =-0.1mA, I_{E} =0	-160	-	-	V
Collector-Emitter Breakdown Voltage	*	V _{(BR)CEO}	$I_C=-1$ mA, $I_B=0$	-150	-	-	V
Emitter-Base Breakdown Voltage		V _{(BR)EBO}	$I_E = -10\mu A, I_C = 0$	-5	-	-	V
DC Current Gain *		h _{FE} (1)	V _{CE} =-5V, I _C =-1mA	50	-	-	
	*	h _{FE} (2)	V _{CE} =-5V, I _C =-10mA	60	-	240	
		h _{FE} (3)	V _{CE} =-5V, I _C =-50mA	50	-	-	
Collector-Emitter * Saturation Voltage	*	V _{CE(sat)} 1	I _C =-10mA, I _B =-1mA	-	-	-0.2	V
		V _{CE(sat)} 2	I_C =-50mA, I_B =-5mA	-	-	-0.5	v
Base-Emitter * Saturation Voltage	*	V _{BE(sat)} 1	I _C =-10mA, I _B =-1mA	-	-	-1.0	V
		V _{BE(sat)} 2	I_C =-50mA, I_B =-5mA	-	-	-1.0	
Transition Frequency		f_T	V _{CE} =-10V, I _C =-10mA, f=100MHz	100	-	300	MHz
Collector Output Capacitance		C_{ob}	V_{CB} =-10V, I_{E} =0, f=1MHz	-	-	6	pF
Small-Signal Current Gain		h _{fe}	V_{CE} =-10V, I_{C} =-1mA, f=1kHz	40	-	200	
Noise Figure		NF	V_{CE} =-5V, I_{C} =-250 μ A Rg=1k Ω , f=10Hz~15.7kHz		-	8	dB

^{*} Pulse Test : Pulse Width ≤ 300 μS, Duty Cycle ≤ 2%.

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.